

# **PSMN016-100PS**

## N-channel 100V 16 $m\Omega$ standard level MOSFET in TO-220

Rev. 3 — 27 September 2011

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in a TO220 packages qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

### 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C	-	-	100	V
$I_D$	drain current	$T_j = 25$ °C; $V_{GS} = 10$ V; see Figure 1	-	-	57	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	148	W
Tj	junction temperature		-55	-	175	°C
Static ch	aracteristics					
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 ^{\circ}\text{C};$ see Figure 12	-	-	28.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 13</u>	-	13	16	mΩ
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	$V_{GS}$ = 10 V; $I_D$ = 30 A; $V_{DS}$ = 50 V;	-	15	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 14; see Figure 15	-	49	-	nC
Avalanch	ne ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 60 A; $V_{sup} \le$ 100 V; unclamped; $R_{GS}$ = 50 $\Omega$	-	-	101	mJ



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		
	S	source		4
mb	D	mounting base; connected to drain		mbb076 S
			SOT78 (TO-220AB)	

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN016-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	100	V
$V_{DGR}$	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	-	40	Α
		$V_{GS}$ = 10 V; $T_j$ = 25 °C; see Figure 1	-	57	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 ^{\circ}C$ ; see Figure 3	-	230	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	148	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
Source-dr	ain diode				
Is	source current	T <sub>mb</sub> = 25 °C	-	57	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	230	Α
Avalanche	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 60 A; $V_{sup} \le$ 100 V; unclamped; $R_{GS}$ = 50 $\Omega$	-	101	mJ
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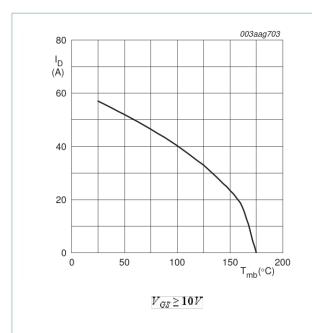


Fig 1. Continuous drain current as a function of mounting base temperature

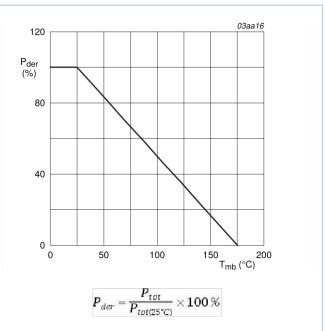
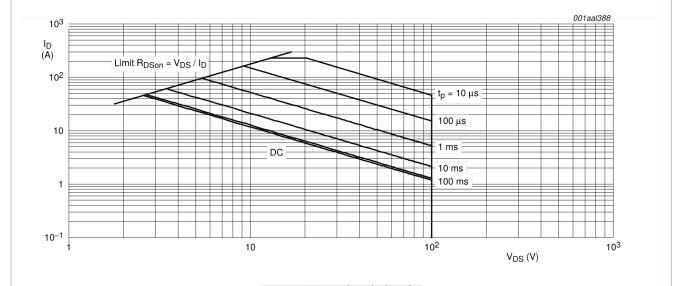


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25$  °C;  $I_{DM}$  is a single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 4	-	0.56	1.01	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		<u>[1]</u> _	50	-	K/W

[1] minimum footprint; mounted on a printed-circuit board to ambient

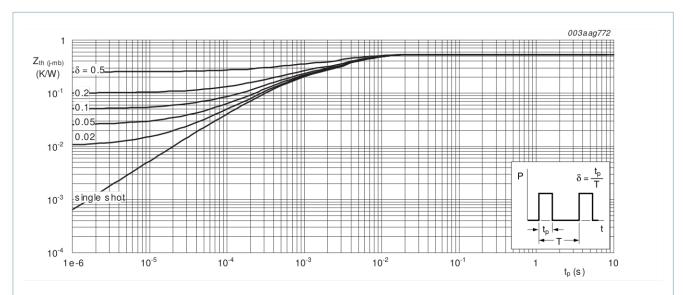


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

### 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	90	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; see <u>Figure 10</u>	1	-	-	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; see Figure 10	-	-	4.8	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 125 °C	-	-	100	μΑ
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.05	5	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	10	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 15 A; $T_j$ = 100 °C; see Figure 12	-	-	28.8	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 15 A; $T_j$ = 175 °C; see Figure 12	-	36.4	44.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 13	-	13	16	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	0.9	-	Ω
Dynamic o	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 0 A$ ; $V_{DS} = 0 V$ ; $V_{GS} = 10 V$ ; see Figure 14	-	40	-	nC
		I <sub>D</sub> = 30 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V;	-	49	-	nC
Q <sub>GS</sub>	gate-source charge	see Figure 14; see Figure 15	-	12	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D$ = 30 A; $V_{DS}$ = 50 V; $V_{GS}$ = 10 V; see Figure 14	-	7.75	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	4.25	-	nC
$Q_{GD}$	gate-drain charge	$I_D$ = 30 A; $V_{DS}$ = 50 V; $V_{GS}$ = 10 V; see Figure 14; see Figure 15	-	15	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V <sub>DS</sub> = 50 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.5	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2404	-	рF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	189	-	рF
C <sub>rss</sub>	reverse transfer capacitance		-	113	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 50 V; $R_{L}$ = 1.7 $\Omega$ ; $V_{GS}$ = 10 V;	-	17	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega; T_j = 25 °C$	-	23	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	36	-	ns
t <sub>f</sub>	fall time		-	18	-	ns

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	in diode					
$V_{SD}$	source-drain voltage	$I_S$ = 15 A; $V_{GS}$ = 0 V; $T_j$ = 25 °C; see Figure 17	-	8.0	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 10 A$ ; $dI_S/dt = 100 A/\mu s$ ;	-	54	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$	-	126	-	nC

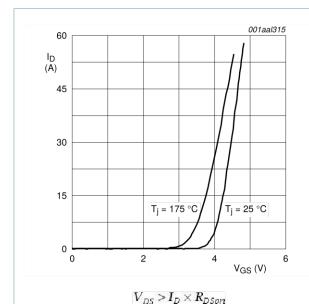


Fig 5. Transfer Characteristic: drain current as a function of gate-source voltage; typical values

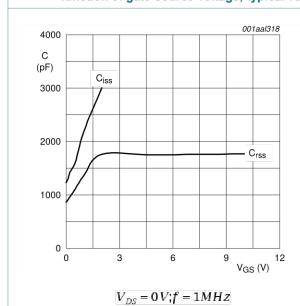
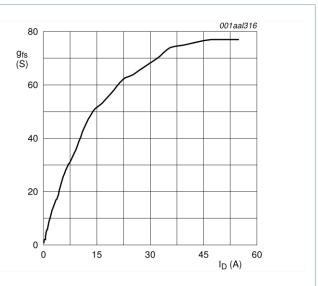
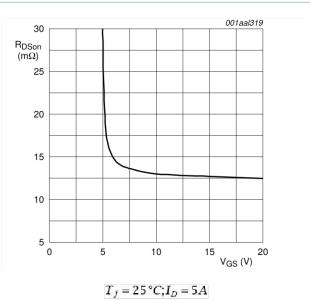


Fig 7. Input and revers transfer capacitances as a function of gate-source voltage; typical values



 $T_J = 25 \,^{\circ}C; V_{DS} = 10 \, V$ 

Fig 6. forward transconductance as a function of drain current; typical values



-j -- -,-b

Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

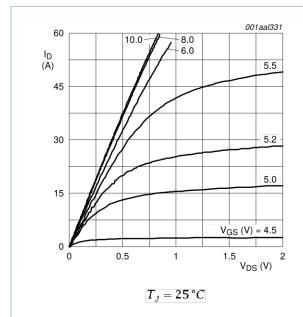


Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values

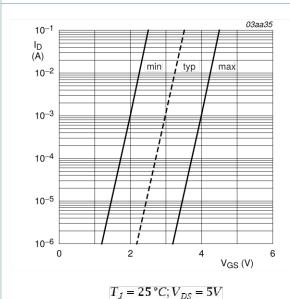


Fig 11. Sub-threshold drain current as a function of gate-source voltage

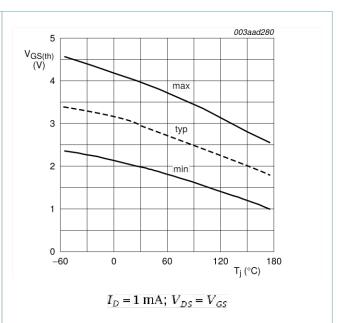


Fig 10. Gate-source threshold voltage as a function of junction temperature

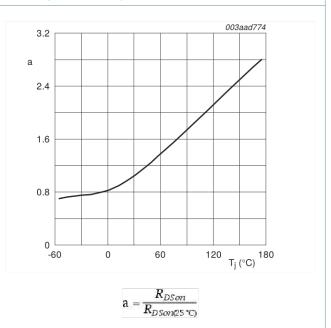


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

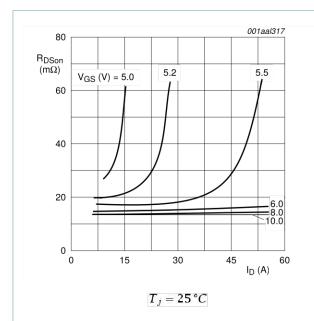


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

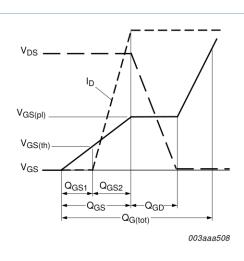
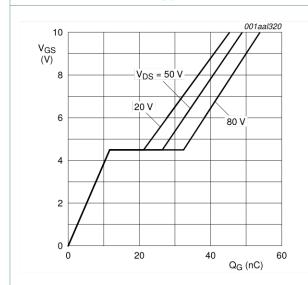
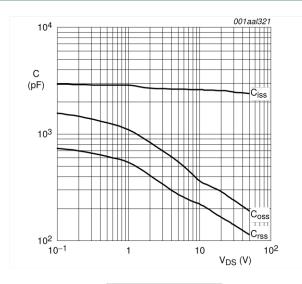


Fig 14. Gate charge waveform definitions



 $T_J = 25 \,^{\circ}C; I_D = 30A$ 

Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

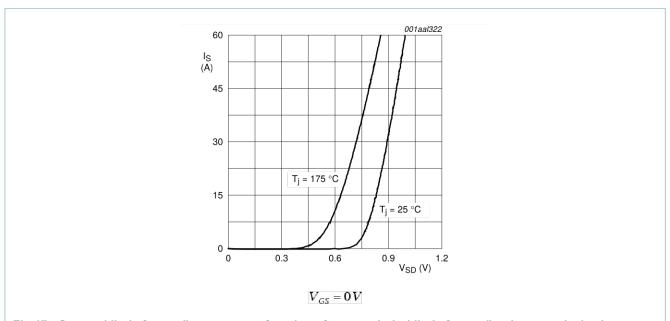
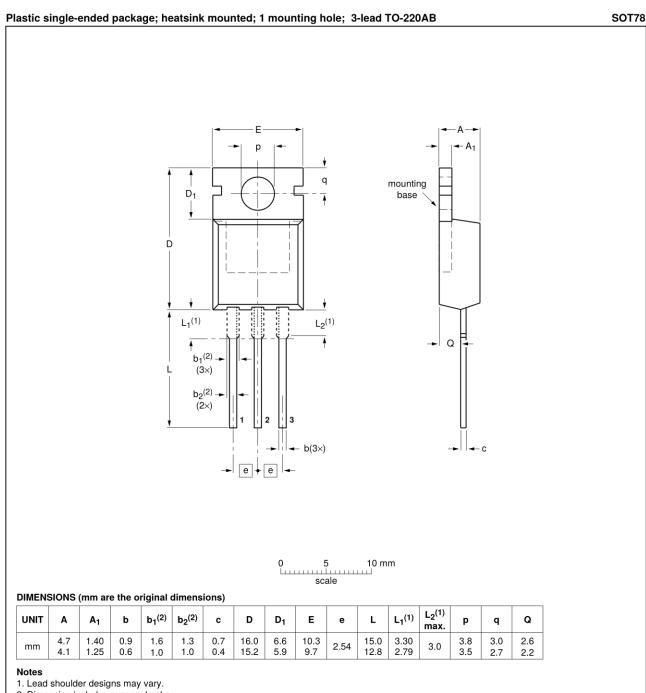


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

### 7. Package outline



2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN ISSUE I	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		<del>08-04-23</del> 08-06-13

Fig 18. Package outline SOT78 (TO-220AB)

PSMN016-100PS

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## 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN016-100PS v.3	20110927	Product data sheet	-	PSMN016-100PS v.2
Modifications:	<ul> <li>Various changes t</li> </ul>	o content.		
PSMN016-100PS v.2	20110721	Product data sheet	-	PSMN016-100PS v.1

### 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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### **PSMN016-100PS**

#### N-channel 100V 16 mΩ standard level MOSFET in TO-220

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# **PSMN016-100PS**

### **Nexperia**

N-channel 100V 16 m $\Omega$  standard level MOSFET in TO-220

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